

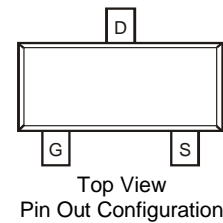
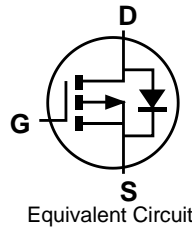
Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max
-200V	80Ω @ V _{GS} = -10V	-65mA

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- DC-DC Converters
- Power Management Functions
- Battery Operated Systems and Solid-State Relays
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.



Features and Benefits

- Low Input Capacitance
- Low Input/Output Leakage
- Small Surface Mount Package
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The ZVP1320FQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**

<https://www.diodes.com/quality/product-definitions/>

Mechanical Data

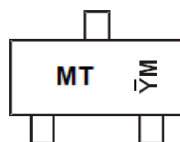
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Alloy 42 Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208^{e3}
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)

Ordering Information (Note 4)

Part Number	Case	Packaging
ZVP1320FQTA	SOT23	3000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



MT = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: 1 = 2021)
 M = Month (ex: 9 = September)

Date Code Key

Year	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032
Code	I	J	K	L	M	N	O	P	R	S	T	U

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	-200	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (Note 6)	I _D	-65	mA
Maximum Body Diode Forward Current (Note 6)	I _S	-65	mA
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	-212	mA
Pulsed Source Current (10µs Pulse, Duty Cycle = 1%)	I _{SM}	-212	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	0.5	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	240	°C/W
Power Dissipation (Note 6)	P _D	0.7	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	180	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-200	—	—	V	V _{GS} = 0V, I _D = -1mA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	µA	V _D = -200V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _D = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	-1.5	—	-3.5	V	V _D = V _{GS} , I _D = -1mA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	51	80	Ω	V _{GS} = -10V, I _D = -30mA
Diode Forward Voltage	V _{SD}	—	-0.7	-1.5	V	V _{GS} = 0V, I _S = -30mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	25	—	pF	V _D = -100V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	9	—		
Reverse Transfer Capacitance	C _{rss}	—	4	—		
Gate Resistance	R _g	—	11.5	—	Ω	f = 1MHz, Level = 50mV, V _{GS} = 5V, V _D = 0V
Total Gate Charge	Q _g	—	1.2	—	nC	V _{GS} = -10V, V _D = -100V I _D = -30mA
Gate-Source Charge	Q _{gs}	—	0.1	—	nC	
Gate-Drain Charge	Q _{gd}	—	0.5	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	4.7	—	ns	V _D = -100V, I _D = -30mA V _{GS} = -10V, R _g = 1Ω
Turn-On Rise Time	t _r	—	7.5	—		
Turn-Off Delay Time	t _{D(OFF)}	—	18.5	—		
Turn-Off Fall Time	t _f	—	140	—		
Body Diode Reverse Recovery Time	t _{RR}	—	81	—	ns	I _F = -1A, di/dt = -100A/µs
Body Diode Reverse Recovery Charge	Q _{RR}	—	210	—	nC	

- Notes:
5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 7. Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to product testing.

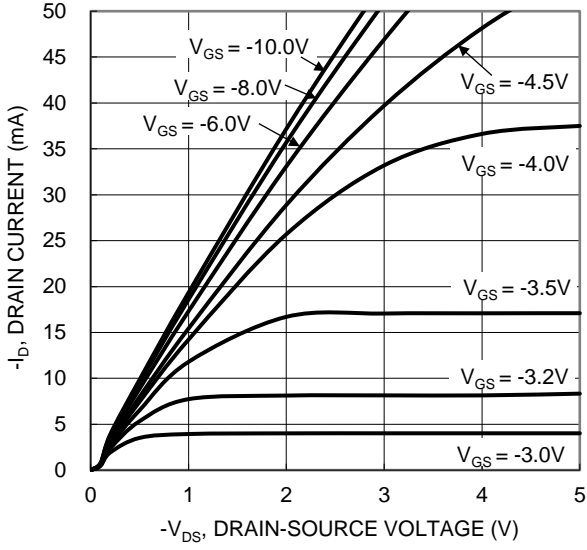


Figure 1. Typical Output Characteristic

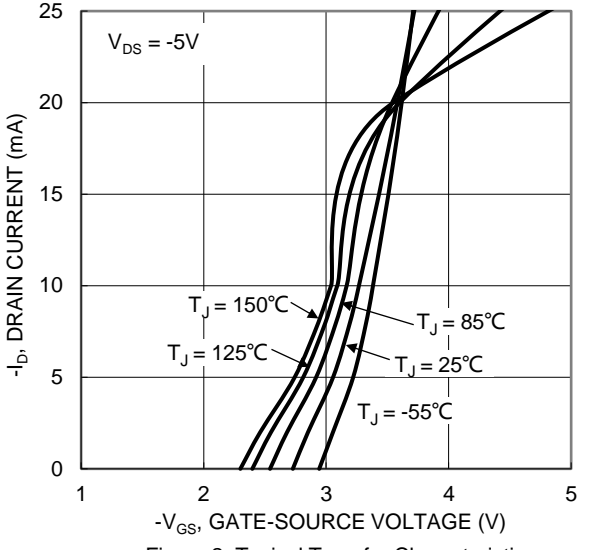


Figure 2. Typical Transfer Characteristic

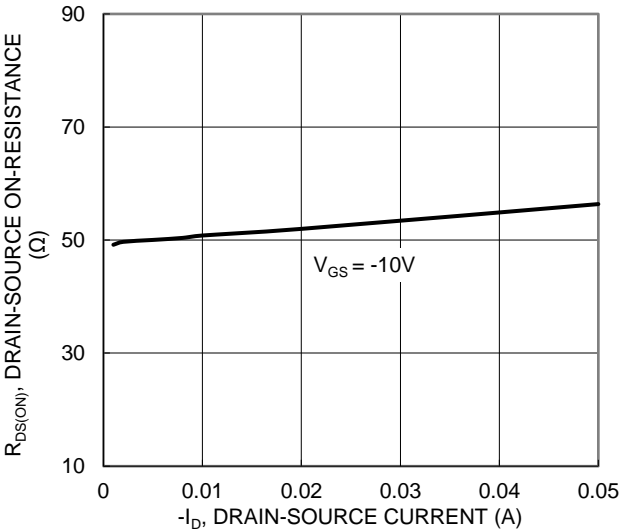


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

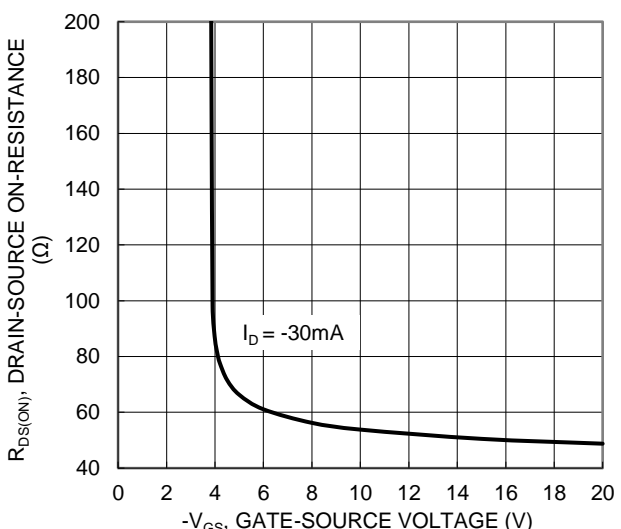


Figure 4. Typical Transfer Characteristic

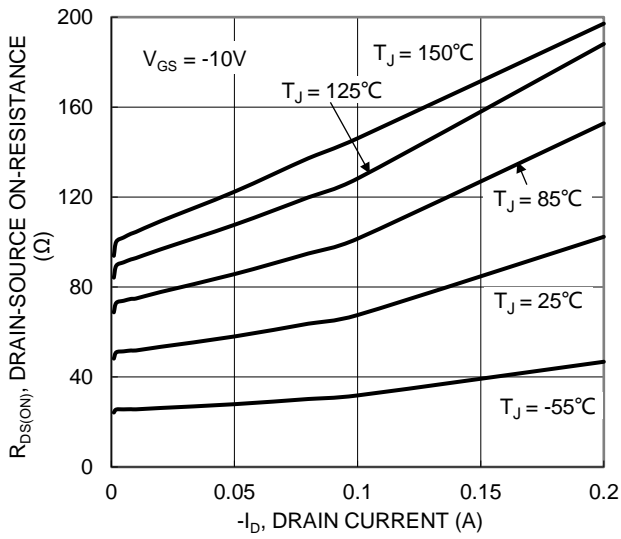


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

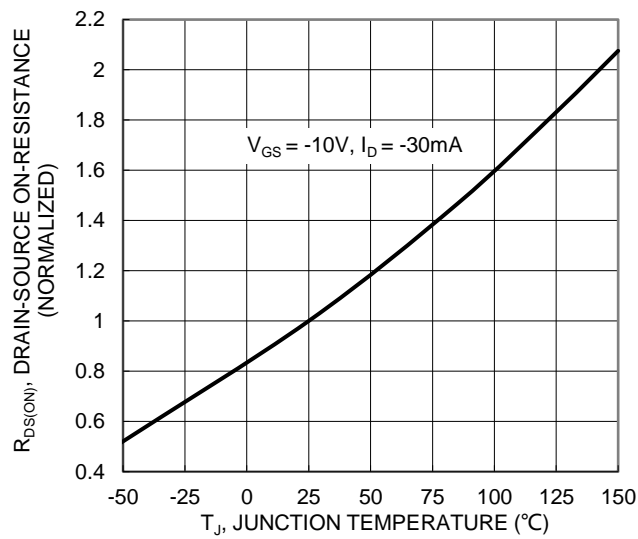
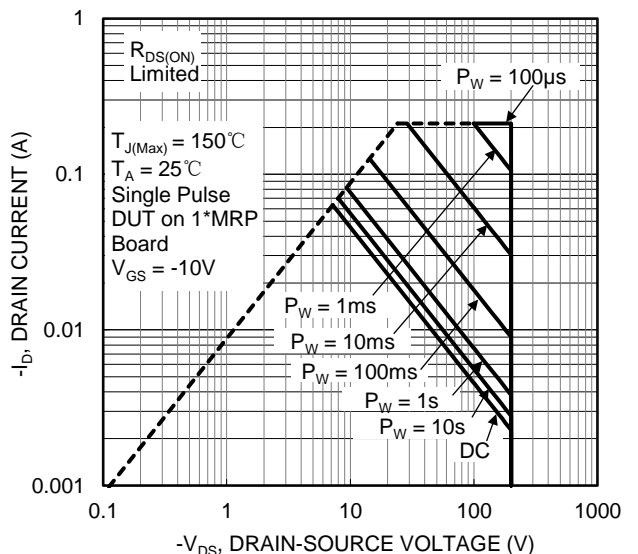
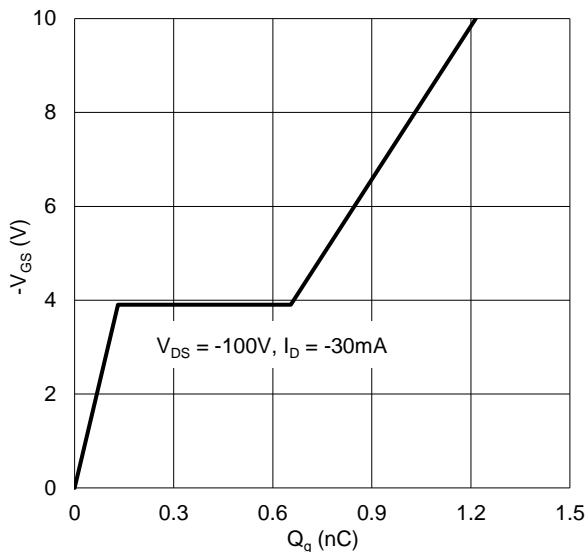
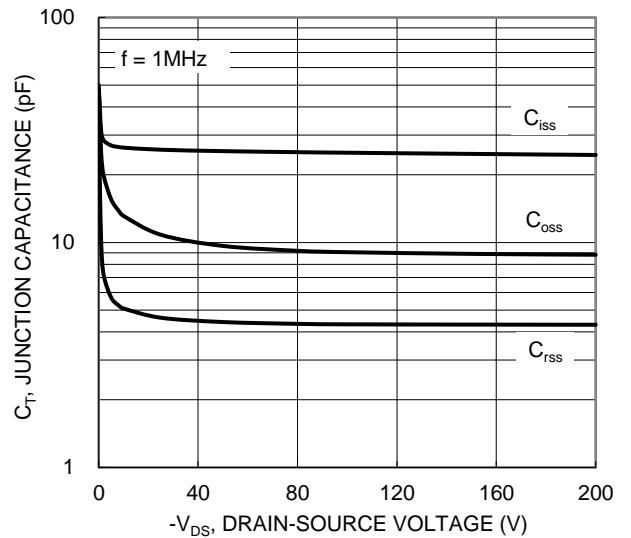
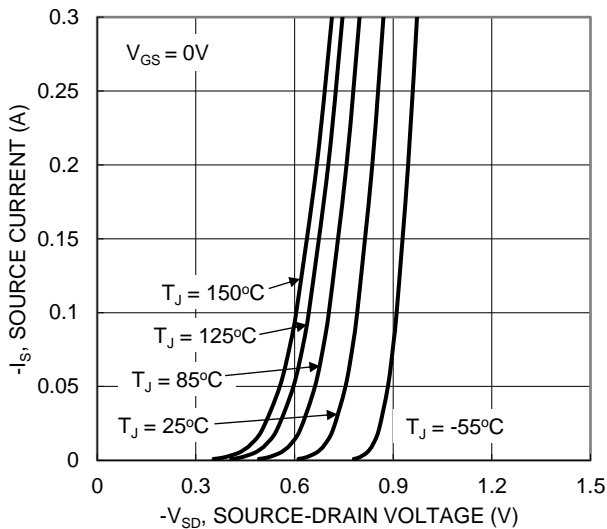
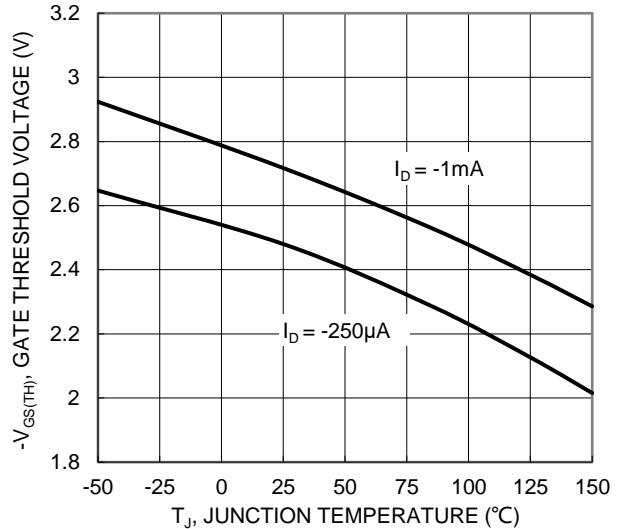
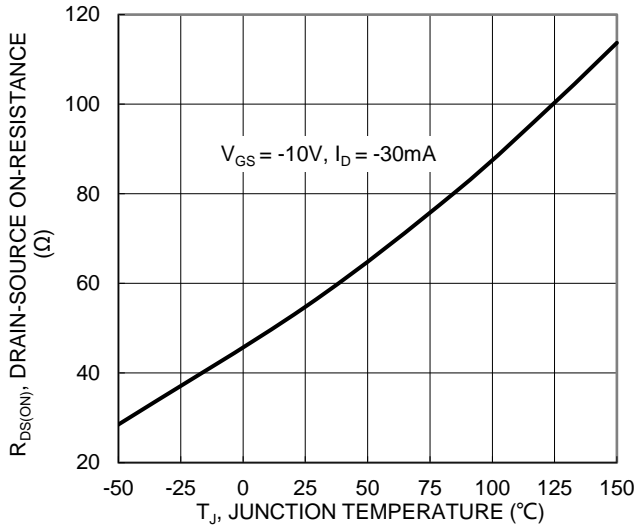


Figure 6. On-Resistance Variation with Junction Temperature



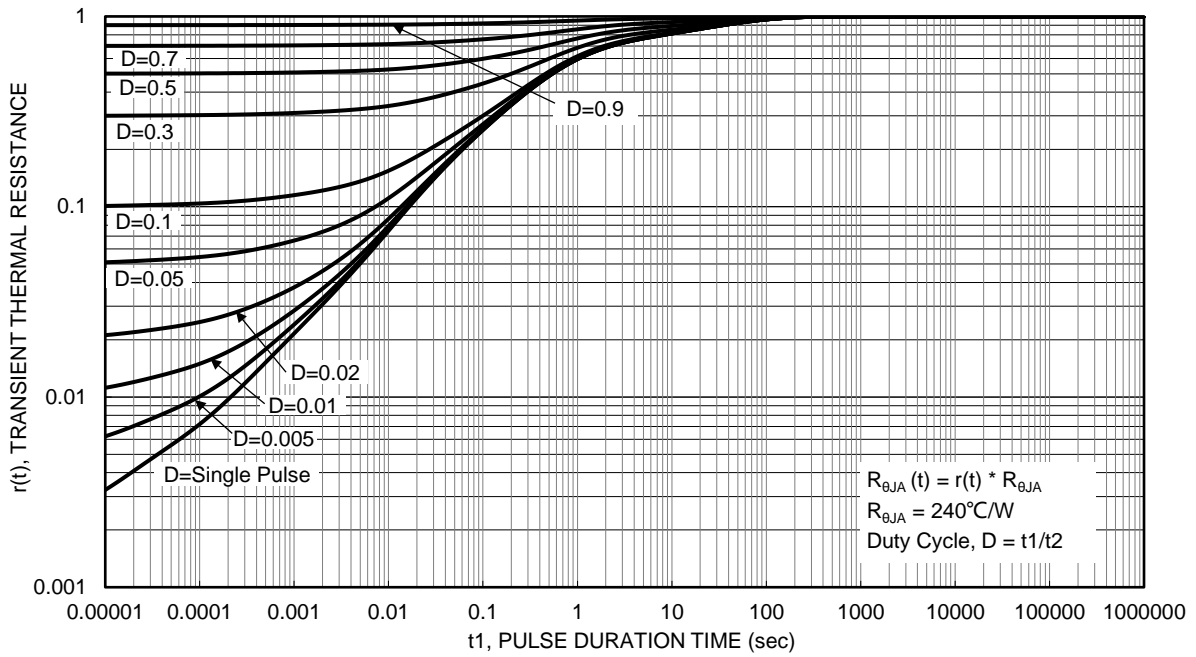
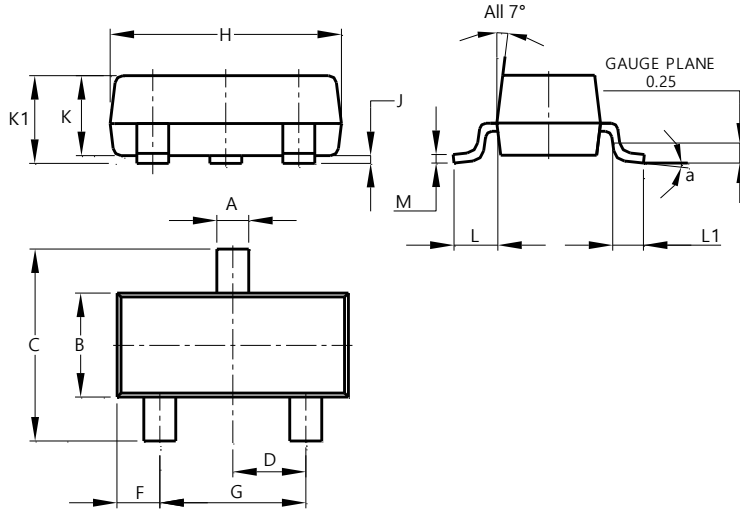


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23

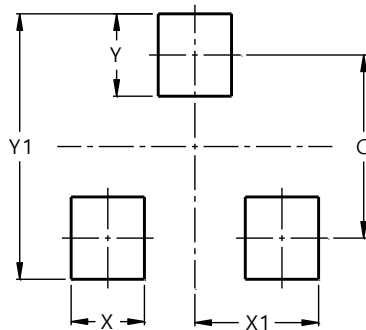


SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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